



**ALPHA & OMEGA**  
SEMICONDUCTOR

**AO8806**

**Common-Drain Dual N-Channel Enhancement Mode Field Effect Transistor**

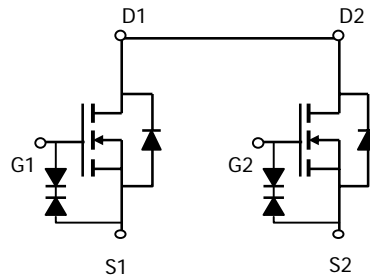
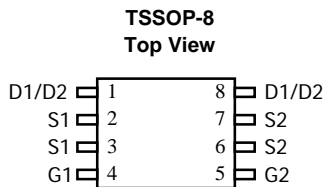


**General Description**

The AO8806 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. *Standard Product AO8806 is Pb-free (meets ROHS & Sony 259 specifications).*

**Features**

- $V_{DS} (V) = 20V$
- $I_D = 7 A (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 22m\Omega (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 27m\Omega (V_{GS} = 2.5V)$
- $R_{DS(ON)} < 35m\Omega (V_{GS} = 1.8V)$



**Absolute Maximum Ratings  $T_A=25^\circ C$  unless otherwise noted**

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$I_D$	A
Pulsed Drain Current <sup>B</sup>	$I_{DM}$	30	
Power Dissipation <sup>A</sup>	$T_A=25^\circ C$ $T_A=70^\circ C$	$P_D$	W
		1	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$			$^\circ C/W$
Maximum Junction-to-Ambient <sup>A</sup>				
Maximum Junction-to-Lead <sup>C</sup>	$R_{\theta JL}$	53	70	$^\circ C/W$

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$ , $V_{GS}=0\text{V}$	20			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=16\text{V}$ , $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			1 5	$\mu\text{A}$
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}$ , $V_{GS}=\pm 4.5\text{V}$ $V_{DS}=0\text{V}$ , $V_{GS}=\pm 8\text{V}$			$\pm 1$ $\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_D=250\mu\text{A}$	0.4	0.6	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}$ , $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}$ , $I_D=7\text{A}$ $T_J=125^\circ\text{C}$		16.5 23	22 29	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}$ , $I_D=5.5\text{A}$		20	27	$\text{m}\Omega$
		$V_{GS}=1.8\text{V}$ , $I_D=5\text{A}$		24	35	$\text{m}\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=5\text{V}$ , $I_D=7\text{A}$		29		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}$ , $V_{GS}=0\text{V}$		0.76	1	V
$I_S$	Maximum Body-Diode Continuous Current				2.5	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}$ , $V_{DS}=10\text{V}$ , $f=1\text{MHz}$		1160		pF
$C_{oss}$	Output Capacitance			187		pF
$C_{rss}$	Reverse Transfer Capacitance			146		pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}$ , $V_{DS}=0\text{V}$ , $f=1\text{MHz}$		1.5		$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=4.5\text{V}$ , $V_{DS}=10\text{V}$ , $I_D=7\text{A}$		16		nC
$Q_{gs}$	Gate Source Charge			0.8		nC
$Q_{gd}$	Gate Drain Charge			3.8		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=5\text{V}$ , $V_{DS}=10\text{V}$ , $R_L=1.35\Omega$ , $R_{GEN}=3\Omega$		6.2		ns
$t_r$	Turn-On Rise Time			12.7		ns
$t_{D(off)}$	Turn-Off DelayTime			51.7		ns
$t_f$	Turn-Off Fall Time			16		ns
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=7\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		17.7		ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=7\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$		6.7		nC

A: The value of  $R_{\theta JA}$  is measured with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to lead  $R_{\theta JL}$  and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

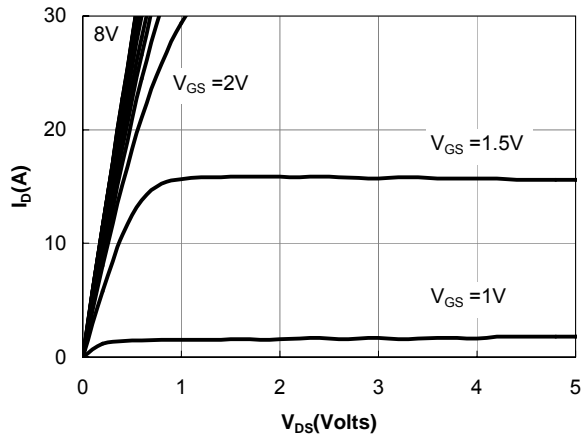


Figure 1: On-Regions Characteristic CS

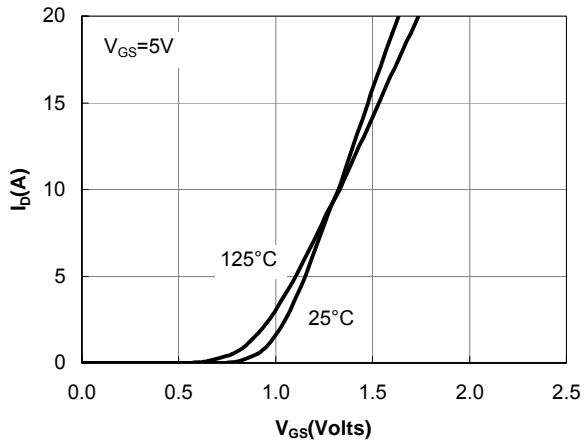


Figure 2: Transfer Characteristics

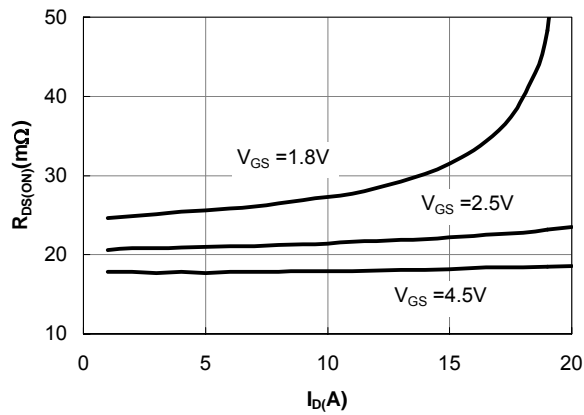


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

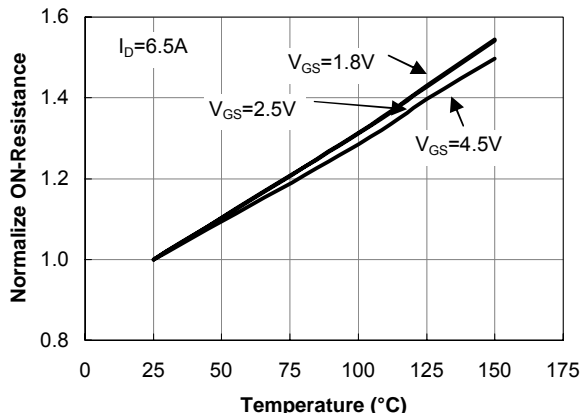


Figure 4: On-Resistance vs. Junction Temperature

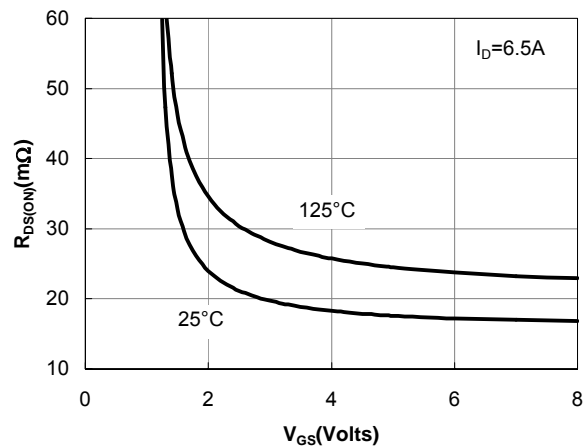


Figure 5: On-Resistance vs. Gate-Source Voltage

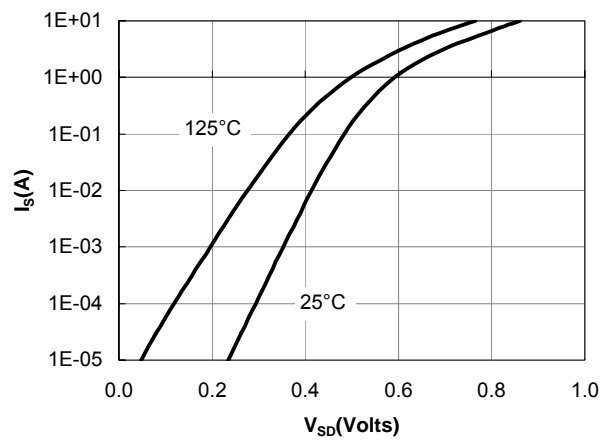


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

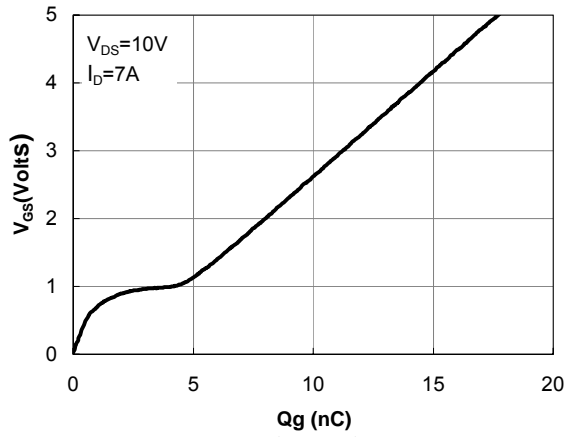


Figure 7: Gate-Charge Characteristics

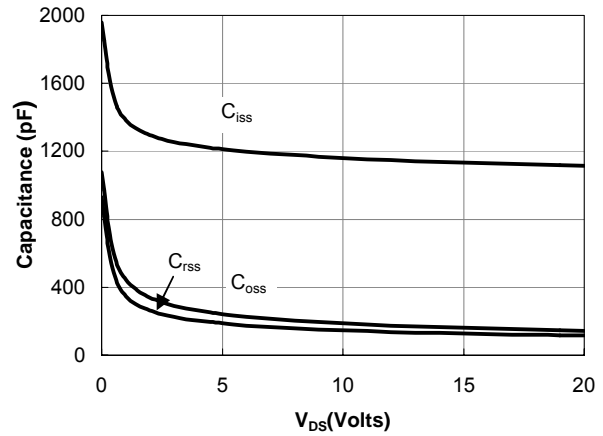


Figure 8: Capacitance Characteristics

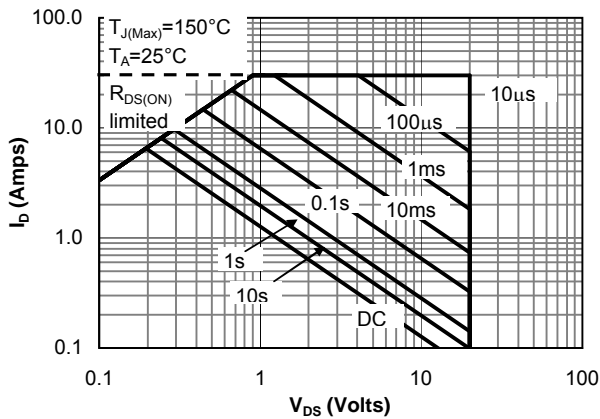


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

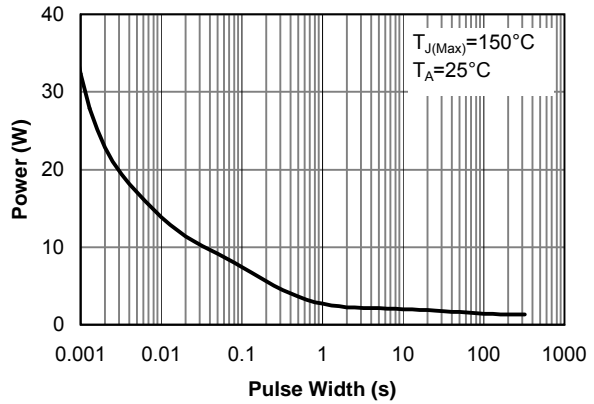


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

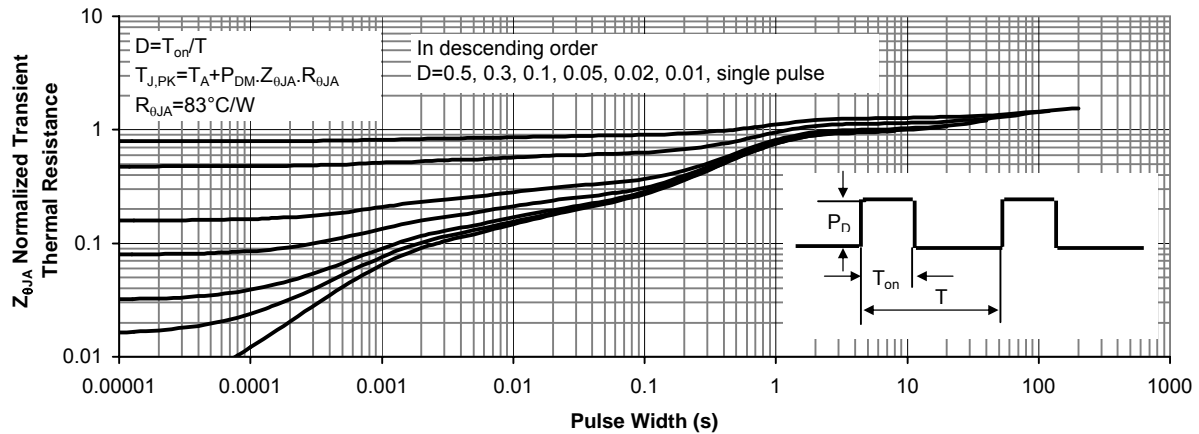


Figure 11: Normalized Maximum Transient Thermal Impedance